

FORM PTO-1449 INFORMATION DISCLOSURE CITATION		Attorney Docket: 1232-4590US2	Serial No.: to be assigned
		Applicants: Yanagita et al.	Examiner: to be assigned
		Filing Date: August 13, 2003	Group Art Unit: to be assigned

U.S. PATENT DOCUMENTS

Examiner Initial		Patent Number	Publication Date	Name	Class	Sub-Class	Filing Date
MAO	AA	3,493,155	02/03/70	Irving Litant et al.	225	2	
MAO	AB	3,549,446	12/22/70	R.W. Bennett et al.	156	230	
MAO	AC	3,667,661	06/06/72	Farmer	225	2	
MAO	AD	3,730,410	05/01/73	Altshuler	225	96.5	
MAO	AE	4,962,879	10/16/90	Goesele et al.	156	281X	
MAO	AF	5,100,544	03/31/92	Izutani, et al.	210	75	
MAO	AG	5,255,853	10/26/93	Munoz	83	177X	
MAO	AH	5,374,564	12/20/94	Bruel	437	24	
MAO	AI	5,379,235	01/03/95	Fisher et al.	364	508	

FOREIGN PATENT DOCUMENTS

Examiner Initial		Patent Number	Publication Date	Country	Class	Sub-Class	Translation
MAO	AJ	KR 1998-33377	0/75/98	Korean	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No
MAO	AK	EP 0 709 876 A1	05/01/96	Europe	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No
MAO	AL	EP 0 840 381 A2	05/06/98	Europe	—	—	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
MAO	AM	EP 0 843 345 A2	5/20/98	Europe	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No

OTHER DOCUMENTS (Including Author, Title, Date, etc.)

MAO	AN	"Single-Crystal Silicon on Non-Single-Crystal Insulators", G.W. Cullen, <u>Journal of Crystal Growth</u> , Vol. 63, No. 3, pp. 429-590, 1983
MAO	AO	"Crystalline Quality of Silicon Layer Formed by FIPOS Technology", Kazuo IMAI et al., <u>Journal of Crystal Growth</u> , Vol. 63, pp 547-553, 1987
MAO	AP	"Silicon-On-Insulator by Wafer Bonding: A Review", W.P. Maszara, <u>Journal of Electrochemical Society</u> , Vol. 138, pp. 341-347, 1991

Examiner	Mark A. Goesele	Date Considered	5-27-04
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP §609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.			

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MAD	AQ	5,510,019	4/23/96	Yabumoto et al.	210	137	
MAD	AR	5,747,387	05/05/98	Koizumi et al.	438	906X	
MAD	AS	5,783,022	07/21/98	Cha et al.	156	344	
MAD	AT	5,849,602	12/15/98	Okamura et al.	438	908X	
MAD	AU	5,876,497	03/02/99	Atoji	117	85	
MAD	AV	5,928,389	7/27/99	Jevtic	29	25.01	
MAD	AW	5,934,856	08/10/99	Asakawa et al.	414	217	
MAD	AX	5,994,207	11/30/99	Henley et al.	438	515	02/19/98
MAD	AY	6,122,566	09/19/00	Nguyen et al.	438	908X	03/03/98

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MAD	AZ	EP 0 999 578 A2	05/10/00	Europe	—	—	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
MAD	BA	EP 1 026 729 A2	08/09/00	Europe	—	—	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
MAD	BB	EP 1 045 448 A1	10/18/00	Europe	—	—	<input type="checkbox"/> Yes <input checked="" type="checkbox"/> No
MAD	BC	EP 0 926 719 A2	06/30/99	Europe	—	—	<input type="checkbox"/> Yes <input checked="" type="checkbox"/> No

OTHER DOCUMENTS (Including Author, Title, Date, etc.)

MAD	BD	"Light Scattering Topography Characterization of Bonded SOI Wafer", H. Baumgart, et al., <u>Extended Abstracts</u> , Vol. 91-2, pp. 733-734, 1991
MAD	BE	"Thinning of Bonded Wafer: Etch-Stop Approaches", Charles E. Hunt et al., <u>Extended Abstracts</u> , Vol. 91-2, pp. 696-697, 1991
MAD	BF	"Epitaxial Layer Transfer by Bond and Etch Back of Porous Si", Takao Yonehara et al., <u>Applied Physics Letters</u> , Vol. 64, pp. 2108-2110, 1994

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MAJ	BG	6,221,740	4/24/01	Bryan et al.	438	458	
MAJ	BH	6,277,234 B1	8/21/01	Freund et al.	156	344	
MAJ	BI	6,321,134 B1	11/20/01	Henley et al.	700	121	11/20/01
MAJ	BJ	5,570,994	11/5/1996	Somekh et al.	414	786	5/10/1995
MAJ	BK	2,191,513	2/27/40	W. P. Bigelow	141	7	3/13/37
MAJ	BL	2,517,394	8/1/50	Z. U. Le Tellier	134	80	2/19/45
MAJ	BM	3,094,207	6/18/63	R. G. Millhiser et al.	198	209	5/24/61
MAJ	BN	3,489,608	1/13/70	B. Jacobs et al.	134	25	10/26/65
MAJ	BO	3,970,471	7/20/76	Bankes et al.	134	6	4/23/75

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Examiner Initial		Document Number	Publication Date	Country	Class	Sub-Class	Translation
MAJ	BP	5-21338	1/29/93	Japan	—	—	English Abstract
MAJ	BQ	7-302889	11/14/95	Japan	—	—	English Abstract
MAJ	BR	WO 99/06110	02/11/99	WO	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No
MAJ	BS	WO 01/04933	01/18/01	WO	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No
MAJ	BT	WO 01/10644 A1	02/15/01	WO	—	—	<input type="checkbox"/> Yes <input type="checkbox"/> No

OTHER DOCUMENTS (Including Author, Title, Date, etc.)

MAJ	BU	"Electrolytic Shaping of Germanium and Silicon", A. Uhlir et al., <u>Bell System Technical Journal</u> , Vol. 35, pp. 333-347, 1956
MAJ	BV	"Oxidized Porous Silicon and It's Application", K. Nagano et al., <u>The Transactions of the Institute of Electronics and Communication Engineers, The Institute of Electronics, Information and Communication</u>
MAJ	BW	"A New Dielectric Isolation Method Using Porous Silicon", K. Imai, <u>Solid-State Electronics</u> , Vol. 224, pp. 159-164, 1981

Examiner Mark A. Ogle Date Considered 5-27-04

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MAO	BX	4,047,973	9/13/77	Williams	134	10	10/27/76
MAO	BY	4,208,760	6/24/80	Dexter et al.	15	302	12/19/77
MAO	BZ	4,215,928	8/5/80	Bayley et al.	354	319	3/30/79
MAO	CA	4,850,381	7/25/89	Moe et al.	134	62	2/1/88
MAO	CB	5,248,886	9/28/93	Asakawa et al.	250	442.11	2/27/92
MAO	CC	5,357,645	10/25/94	Onodera	15	97.1	5/14/93
MAO	CD	5,653,247	8/5/1997	Murakami	134	80	8/14/95
MAO	CE	5,679,405	10/21/97	Thomas et al.	427	248.1	7/24/95
MAO	CF	5,792,709	8/11/98	Robinson et al.	438	692	12/19/95

FOREIGN PATENT DOCUMENTS

Examiner Initial		Patent Number	Publication Date	Country	Class	Sub-Class	Translation
MAO	CG	JPA 56-30650	3/27/81	Japan	✓	—	Abstract Only
MAO	CH	JPA60-05530	1/14/94	Japan	—	—	English Abstract
MAO	CI	JPA4-293236	10/16/92	Japan	✓	—	English Abstract

OTHER DOCUMENTS (Including Author, Title, Date, etc.)

MAO	CJ	"Silicon on Insulator Material by Wafer Bonding", Christine Harendt, Charles E. Hunt et al., <i>Journal of Electronic Materials</i> , vol. 20, pp. 267-277, 1991
MAO	CK	Michel Bruel, et al. "Smart-Cut: A New Silicon On Insulator Material Technology Based On Hydrogen Implantation And Wafer Bonding", Jpn. J. Appl. Phys. Vol. 36, No. 3B, Part 01, March 1, 1997, pages 1636-1641.
MAO	CL	U.S. Application Serial No. 09/399,643, filed September 20, 2002, entitled "Separating Apparatus and Method, and Substrate Manufacturing Method."

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MAD	CM	5,795,401	8/18/98	Itoh et al.	134	6	10/10/96
MAD	CN	5,810,028	9/22/98	Ichikawa et al.	134	66	6/12/97
MAD	CO	5,820,329	10/13/98	Derbinski et al.	414	225	4/10/97
MAD	CP	5,954,888	9/21/99	Gupta et al.	134	3	2/9/98
MAD	CQ	6,007,675	12/28/99	Toshima	156	345	12/1/97
MAD	CR	6,168,499	1/2/2001	Jang	451	8	5/18/99
MAD	CS	4,915,564	4/10/90	Eror et al.	414	217	7/20/98
MAD	CT	6,131,589	10/17/00	Vogtmann et al.	134	113	2/9/99
MAD	CU	6,382,292	5/7/02	Ohmi et al.	156	584	3/25/98
MAD	CV	6,418,999	7/16/02	Yanagita et al.	156	584	12/15/98
MAD	CW	6,527,031	3/4/03	Yanagita et al	156	584	11/5/99

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Examiner Initial		Patent Number	Publication Date	Country	Class	Sub-Class	Translation
MAD	CX	JPA63-16455	11/15/94	Japan	—	—	English Abstract
MAD	CY	JPA9-167724	6/24/97	Japan	—	—	English Abstract
	CZ						<input type="checkbox"/> Yes <input type="checkbox"/> No

OTHER DOCUMENTS (Including Author, Title, Date, etc.)

MAD	DA	U.S. Application Serial No. 09/434,740, filed November 11, 2002, entitled "Sample Separating Apparatus and Method."
MAD	DB	U.S Application No. 09/434,663, filed November 5, 1999, entitled "Sample Processing System," to K. Yanagita et al.
MAD	DC	"History of Water Jet Machining Development", Journal of the Water Jet Technology Society of Japan, vol. 1, No. 1, 1984, pages 4-15.

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